

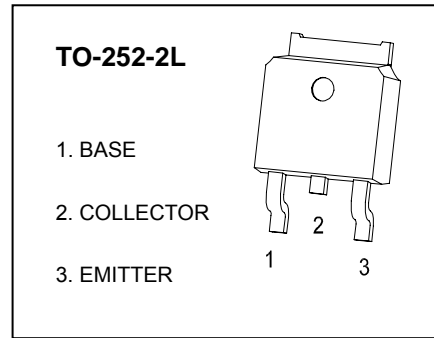


TO-252-2L Plastic-Encapsulate Transistors

2SC3303 TRANSISTOR (NPN)

FEATURES

- Low Collector Saturation Voltage
- High Speed Switching Time



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	100	V
V _{CE0}	Collector-Emitter Voltage	80	V
V _{EBO}	Emitter-Base Voltage	7	V
I _C	Collector Current	5	A
P _C	Collector Power Dissipation	1	W
R _{θJA}	Thermal Resistance From Junction To Ambient	125	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μA, I _E =0	100			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =10mA, I _B =0	80			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	7			V
Collector cut-off current	I _{CBO}	V _{CB} =100V, I _E =0			1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =7V, I _C =0			1	μA
DC current gain	h _{FE(1)}	V _{CE} =1V, I _C =1A	70		240	
	h _{FE(2)}	V _{CE} =1V, I _C =3A	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =3A, I _B =150mA			0.4	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =3A, I _B =150mA			1.2	V
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		80		pF
Transition frequency	f _T	V _{CE} =4V, I _C =1A,		20		MHz

CLASSIFICATION OF h_{FE(1)}

RANK	O	Y
RANGE	70-140	120-240

Typical Characteristics

2SC3303

